

HEF4555B-Q100

1-of-4 decoder/demultiplexer

Rev. 1 — 21 October 2013

Product data sheet

1. General description

The HEF4555B-Q100 contains two 1-of-4 decoders/demultiplexers. Each decoder/demultiplexer has two address inputs, nA0 and nA1. They also have an active LOW enable input (\overline{nE}) and four mutually exclusive outputs which are active HIGH (nY0 to nY3). When used as a decoder, \overline{nE} when HIGH, forces nY0 to nY3 LOW. When used as a demultiplexer, the information on nA0 and nA1 with \overline{nE} as data input selects the appropriate output. All unselected outputs are LOW.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 3) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 3)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Complies with JEDEC standard JESD 13-B

3. Applications

- Code conversion
- Address decoding
- Demultiplexing: when using the enable input as data input



4. Ordering information

Table 1. Ordering information
All types operate from -40 °C to +85 °C.

Type number	Package		Version
	Name	Description	
HEF4555BT-Q100	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1

5. Functional diagram

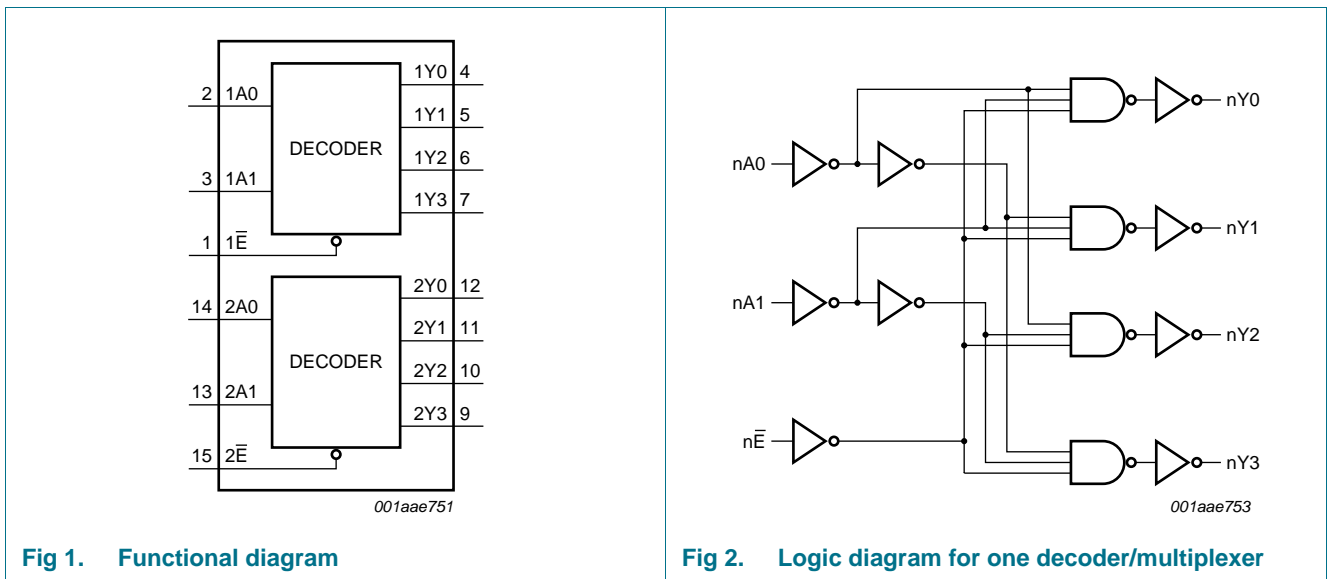


Fig 1. Functional diagram

Fig 2. Logic diagram for one decoder/multiplexer

6. Pinning information

6.1 Pinning

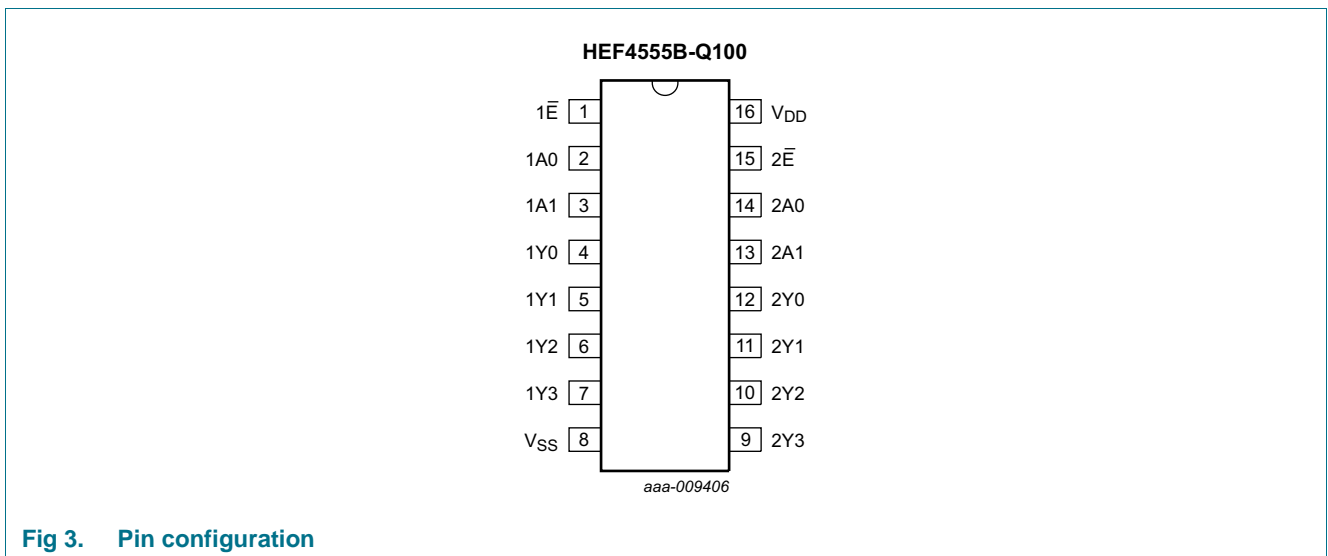


Fig 3. Pin configuration

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A0, 1A1, 2A0, 2A1	2, 3, 14, 13	address input
1E, 2E	1, 15	enable input (active LOW)
1Y0, 1Y1, 1Y2, 1Y3, 2Y0, 2Y1, 2Y2, 2Y3	4, 5, 6, 7, 12, 11, 10, 9	output (active HIGH)
V _{DD}	16	supply voltage
V _{SS}	8	ground (GND)

7. Functional description

Table 3. Function selection^[1]

Inputs			Outputs			
nE	nA0	nA1	nY0	nY1	nY2	nY3
L	L	L	H	L	L	L
L	H	L	L	H	L	L
L	L	H	L	L	H	L
L	H	H	L	L	L	H
H	X	X	L	L	L	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{DD} + 0.5 V	-	±10	mA
V _I	input voltage		-0.5	V _{DD} + 0.5	V
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{DD} + 0.5 V	-	±10	mA
I _{I/O}	input/output current		-	±10	mA
I _{DD}	supply current		-	50	mA
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		-40	+85	°C
P _{tot}	total power dissipation	T _{amb} -40 °C to +85 °C	^[1] -	500	mW
P	power dissipation	per output	-	100	mW

[1] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5\text{ V}$	-	-	3.75	$\mu\text{s/V}$
		$V_{DD} = 10\text{ V}$	-	-	0.5	$\mu\text{s/V}$
		$V_{DD} = 15\text{ V}$	-	-	0.08	$\mu\text{s/V}$

10. Static characteristics

Table 6. Static characteristics

$V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40\text{ °C}$		$T_{amb} = 25\text{ °C}$		$T_{amb} = 85\text{ °C}$		Unit			
				Min	Max	Min	Max	Min	Max				
V_{IH}	HIGH-level input voltage	$ I_O < 1\ \mu\text{A}$	5 V	3.5	-	3.5	-	3.5	-	V			
			10 V	7.0	-	7.0	-	7.0	-	V			
			15 V	11.0	-	11.0	-	11.0	-	V			
V_{IL}	LOW-level input voltage	$ I_O < 1\ \mu\text{A}$	5 V	-	1.5	-	1.5	-	1.5	V			
			10 V	-	3.0	-	3.0	-	3.0	V			
			15 V	-	4.0	-	4.0	-	4.0	V			
V_{OH}	HIGH-level output voltage	$ I_O < 1\ \mu\text{A}$; $V_I = V_{SS}$ or V_{DD}	5 V	4.95	-	4.95	-	4.95	-	V			
			10 V	9.95	-	9.95	-	9.95	-	V			
			15 V	14.95	-	14.95	-	14.95	-	V			
V_{OL}	LOW-level output voltage	$ I_O < 1\ \mu\text{A}$; $V_I = V_{SS}$ or V_{DD}	5 V	-	0.05	-	0.05	-	0.05	V			
			10 V	-	0.05	-	0.05	-	0.05	V			
			15 V	-	0.05	-	0.05	-	0.05	V			
I_{OH}	HIGH-level output current	$V_O = 2.5\text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	mA			
			5 V	-	-0.52	-	-0.44	-	-0.36	mA			
			10 V	-	-1.3	-	-1.1	-	-0.9	mA			
			15 V	-	-3.6	-	-3.0	-	-2.4	mA			
I_{OL}	LOW-level output current	$V_O = 0.4\text{ V}$	5 V	0.52	-	0.44	-	0.36	-	mA			
			10 V	1.3	-	1.1	-	0.9	-	mA			
			15 V	3.6	-	3.0	-	2.4	-	mA			
I_I	input leakage current	$V_{DD} = 15\text{ V}$	15 V	-	± 0.3	-	± 0.3	-	± 1.0	μA			
			I_{DD}	supply current	$I_O = 0\text{ A}$; $V_I = V_{SS}$ or V_{DD}	5 V	-	20	-	20	-	150	μA
						10 V	-	40	-	40	-	300	μA
C_I	input capacitance		15 V	-	80	-	80	-	600	μA			
			-	-	-	-	7.5	-	-	pF			

11. Dynamic characteristics

Table 7. Dynamic characteristics

$V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ °C}$; for test circuit, see [Figure 5](#); unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay	nAn → nYn; see Figure 4	5 V	[1] $88\text{ ns} + (0.55\text{ ns/pF})C_L$	-	115	230	ns
			10 V	$34\text{ ns} + (0.23\text{ ns/pF})C_L$	-	45	90	ns
			15 V	$22\text{ ns} + (0.16\text{ ns/pF})C_L$	-	30	65	ns
		n \bar{E} → nYn	5 V	$98\text{ ns} + (0.55\text{ ns/pF})C_L$	-	125	250	ns
			10 V	$39\text{ ns} + (0.23\text{ ns/pF})C_L$	-	50	95	ns
			15 V	$22\text{ ns} + (0.16\text{ ns/pF})C_L$	-	30	65	ns
t_{PLH}	LOW to HIGH propagation delay	nAn → nYn	5 V	[1] $113\text{ ns} + (0.55\text{ ns/pF})C_L$	-	140	280	ns
			10 V	$44\text{ ns} + (0.23\text{ ns/pF})C_L$	-	55	105	ns
			15 V	$32\text{ ns} + (0.16\text{ ns/pF})C_L$	-	40	75	ns
		n \bar{E} → nYn	5 V	$123\text{ ns} + (0.55\text{ ns/pF})C_L$	-	150	295	ns
			10 V	$44\text{ ns} + (0.23\text{ ns/pF})C_L$	-	55	110	ns
			15 V	$32\text{ ns} + (0.16\text{ ns/pF})C_L$	-	40	75	ns
t_t	transition time	on nYn	5 V	[1][2] $10\text{ ns} + (1.00\text{ ns/pF})C_L$	-	60	120	ns
			10 V	$9\text{ ns} + (0.42\text{ ns/pF})C_L$	-	30	60	ns
			15 V	$6\text{ ns} + (0.28\text{ ns/pF})C_L$	-	20	40	ns

[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

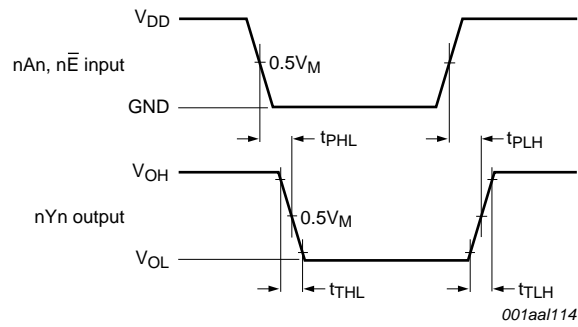
[2] Transition time t_t is the same as the HIGH to LOW and LOW to HIGH transition times t_{THL} and t_{TLH} .

Table 8. Dynamic power dissipation P_D

P_D can be calculated from the formulas shown. $V_{SS} = 0\text{ V}$; $t_r = t_f \leq 20\text{ ns}$; $T_{amb} = 25\text{ °C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μW)	Where:
P_D	dynamic power dissipation	5 V	$P_D = 4500 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz,
		10 V	$P_D = 18800 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_o = output frequency in MHz,
		15 V	$P_D = 45700 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF, V_{DD} = supply voltage in V, $\Sigma(f_o \times C_L)$ = sum of the outputs.

12. Waveforms



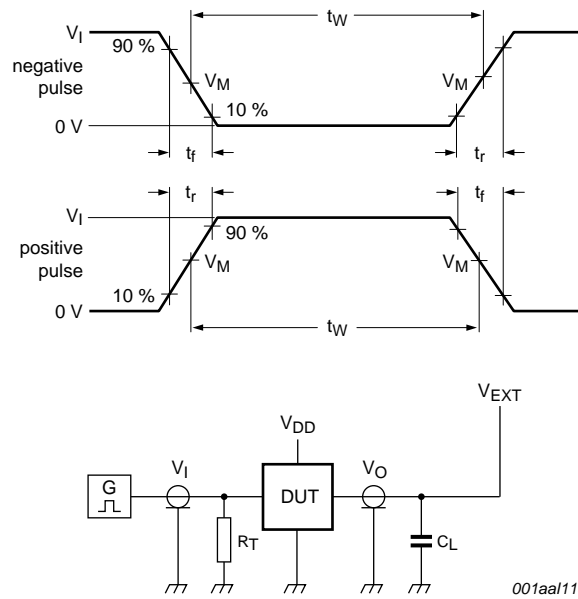
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 4. Inputs nA_n and $n\bar{E}$ to output nY_n propagation delays

Table 9. Measurement points

Supply voltage	Input	Output
V_{DD}	V_M	V_M
5 V to 15 V	$0.5V_{DD}$	$0.5V_{DD}$



Test data is given in [Table 10](#).

Definitions for test circuit:

Device Under Test (DUT);

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator;

V_{EXT} = External voltage for measuring switching times.

Fig 5. Load circuitry for switching times

Table 10. Test data

Supply voltage	Input		Load	V_{EXT}	
	V_I	$t_r = t_f$	C_L	t_{PLH}, t_{PHL}	t_{THL}, t_{TLH}
5 V to 15 V	V_{DD}	≤ 20 ns	50 pF	open	V_{DD}

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

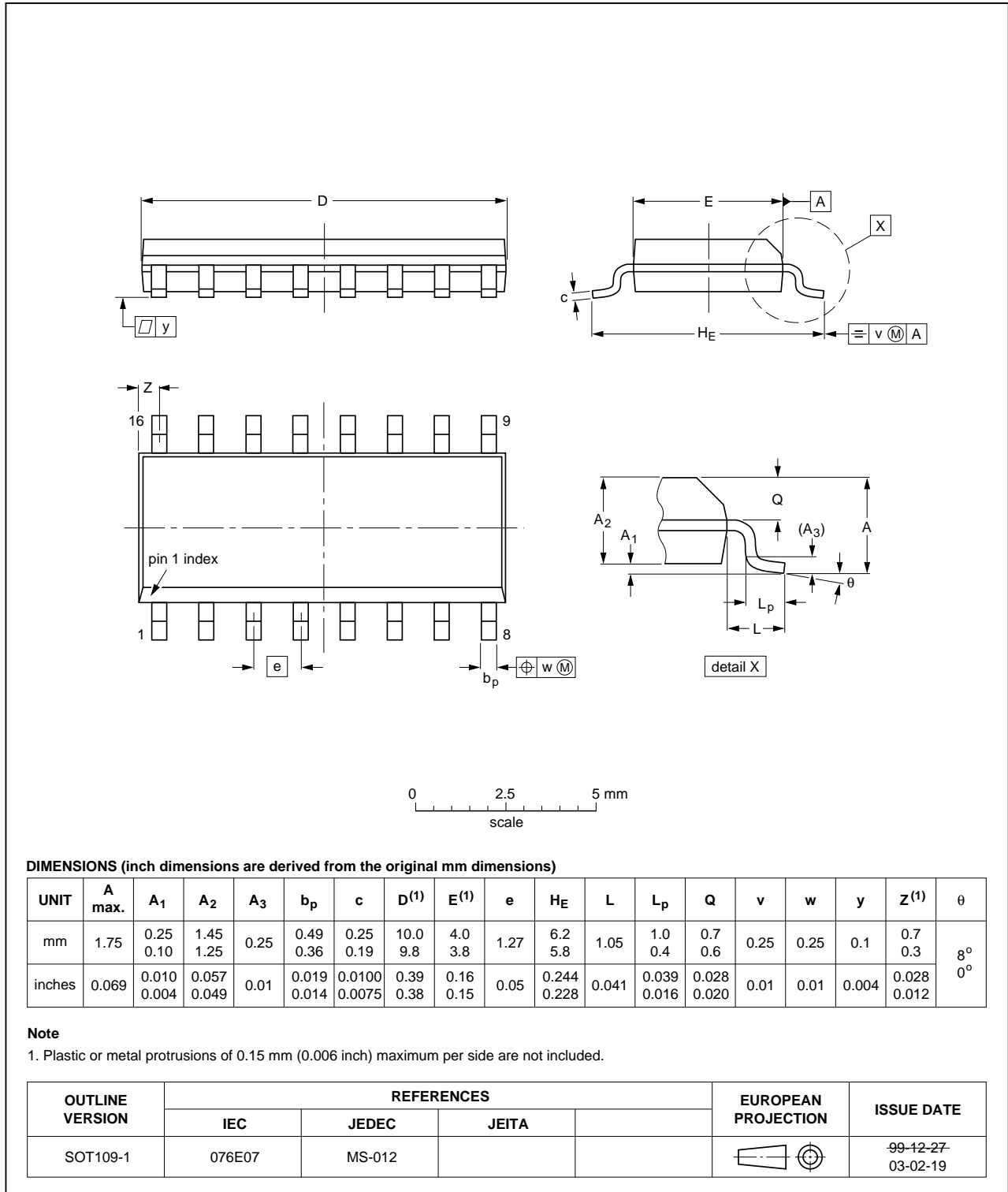


Fig 6. Package outline SOT109-1 (SO16)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4555B_Q100 v.1	20131021	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

16.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

18. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Ordering information	2
5	Functional diagram	2
6	Pinning information	2
6.1	Pinning	2
6.2	Pin description	3
7	Functional description	3
8	Limiting values	3
9	Recommended operating conditions	4
10	Static characteristics	4
11	Dynamic characteristics	5
12	Waveforms	6
13	Package outline	8
14	Abbreviations	9
15	Revision history	9
16	Legal information	10
16.1	Data sheet status	10
16.2	Definitions	10
16.3	Disclaimers	10
16.4	Trademarks	11
17	Contact information	11
18	Contents	12

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2013.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 21 October 2013

Document identifier: HEF4555B_Q100